Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.8)	V_{pp}	3	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =150 R_L =3.3kΩ	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	50	mA
				70	
I_H	I_T =100mA		MAX.	45	mA
dV/dt	V_D=540V Gate Open T_j =150		MIN.	1000	V/μs
(dI/dt)c	(dV/dt)c=20V/μs, T_j=150		MIN.	5	A/ms
t_{on}	I_G=40mA I_A=200mA I_R=20mA T_j=25		TYP.	3	μs
t_{off}				30	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM} =11A t_p=380μs	T_j=25	1.4	V
V_{TO}	Threshold voltage	T_j=150	0.79	V
R_D	Dynamic resistance	T_j=150	51	mΩ

I_{DRM}

V_D =V_{DRM} V_R =V_{RRM} V

FIG.1: Maximum power dissipation versus axim (TE)-0 T10.199.4668 0.4onM

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

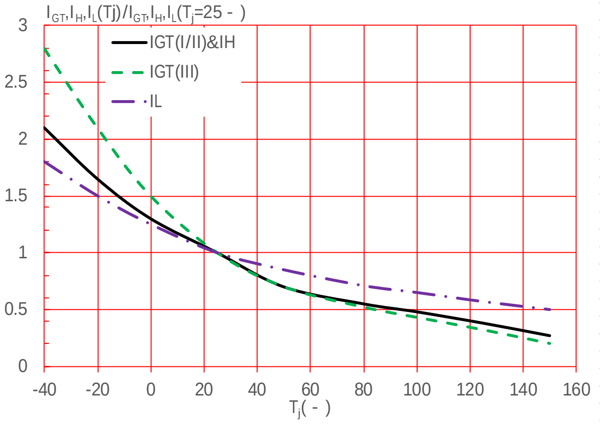
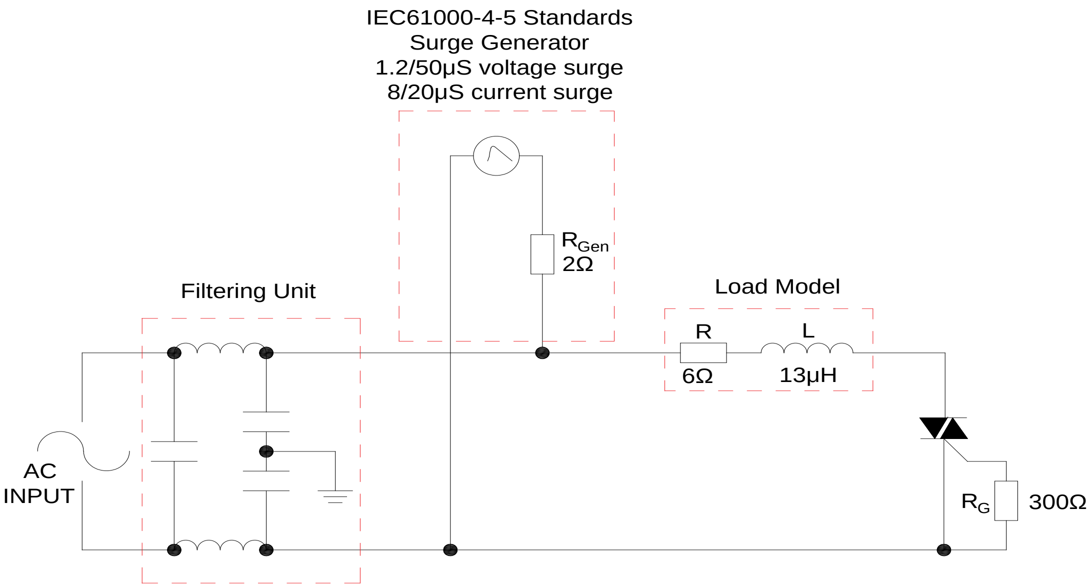
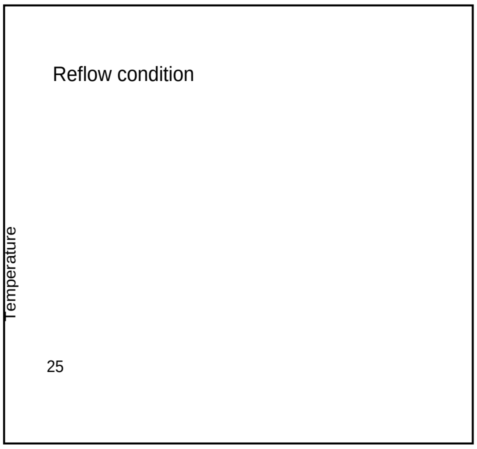


FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SOLDERING PARAMETERS

Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150
	-Temperature Max($T_{s(max)}$)	+200
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquidus Temp (T_L)to peak)		3 /sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3 /sec. Max
Reflow	-Temperature(T_L)(Liquidus)	+217
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)
Time within 5 of actual Peak Temp (t_p)		20-40secs.
Ramp-down Rate		6 /sec. Max
Time 25 to Peak Temp (T_P)		8 min. Max
Do not exceed		+260



ORDERING INFORMATION

PACKAGE MECHANICAL DATA

	Dimensions					
Ref.	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.40		9.60	0.370		0.378
D	2.40			0.094		
E	1.20		1.50	0.047(0)]TJ	0 Tc	0 Tw 31G
F						

T835H-8E